

SN74LVC1G08-Q1 单路双输入正与门

1 特性

- 符合面向汽车应用的 AEC-Q100 标准：
 - 器件温度等级 1: -40°C 至 $+125^{\circ}\text{C}$, T_A
- 支持 5V V_{CC} 运行
- 过压容差输入最高可达 5.5V
- 支持向下转换到 V_{CC}
- 低功耗, I_{CC} 最大值为 $10\mu\text{A}$
- 电压为 3.3V 时, 输出驱动为 $\pm 24\text{mA}$
- I_{off} 支持带电插入、局部断电模式和后驱动保护
- 闩锁性能超过 100mA, 符合 JESD 78 II 类规范
- ESD 保护性能超过 JESD 22 规范要求
 - 2000V 人体放电模型 (A114-A)
 - 200V 机器模型 (A115-A)
 - 1000V 充电器件模型 (C101)

2 应用

- 完全符合汽车类应用的标准
- 将多个电源轨的电源正常信号相结合
- 在条件为真时传递信号
- 将低电平有效误差信号进行结合

3 说明

按照设计, 此单路双输入正与门可在 1.65V 至 5.5V V_{CC} 电压下运行。

SN74LVC1G08-Q1 器件以正逻辑执行布尔函数或 $Y = A \cdot B$ or $Y = \overline{A + B}$ 。

该器件完全适用于使用 I_{off} 的局部断电应用。 I_{off} 电路会禁用输出, 从而在器件断电时防止电流回流损坏器件。

CMOS 器件具有高输出驱动, 同时在宽 V_{CC} 工作范围内保持低静态功率耗散。

SN74LVC1G08 采用多种封装, 包括封装尺寸为 $1.45\text{mm} \times 1.00\text{mm}$ 的小型 DRY 封装。

器件信息⁽¹⁾

器件名称	封装	封装尺寸
SN74LVC1G08Q	SOT-23 (5)	$2.90\text{mm} \times 1.60\text{mm}$
	SC70 (5)	$2.00\text{mm} \times 1.25\text{mm}$
	SON (6)	$1.45\text{mm} \times 1.00\text{mm}$

(1) 如需了解所有可用封装, 请参阅产品说明书末尾的可订购产品附录。



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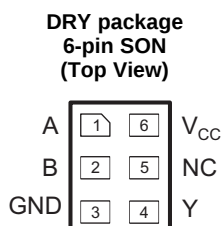
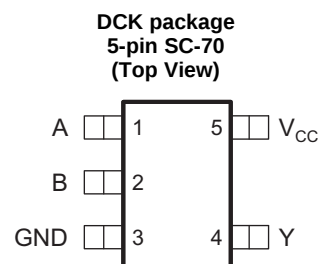
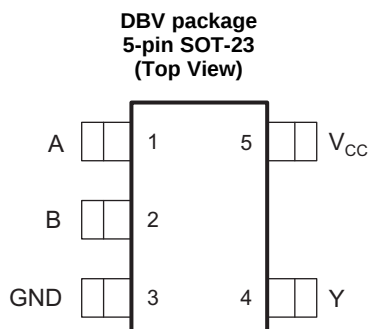
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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision F (April 2008) to Revision G	Page
• 已更改 将数据表更改为新的 TI 格式	1
• 已添加 向器件信息 表添加了 DRY 封装	1
• Added <i>Thermal Information</i> table.	5
• Added <i>Typical Characteristics</i>	7
• Added <i>Detailed Description</i> section.	10
• Added <i>Application and Implementation</i> section.	11
• Added <i>Power Supply Recommendations</i> section.	12
• Added <i>Layout</i> section.	12

5 Pin Configuration and Functions



NC – No internal connection

See mechanical drawings for dimensions.

Pin Functions

PIN			I/O	DESCRIPTION
NAME	NO. DBV, DCK	NO. DRY		
A	1	1	Input	Input A
B	2	2	Input	Input B
GND	3	3	—	Ground
Y	4	4	Output	Output Y
V _{CC}	5	6	—	Positive Supply
NC		5	—	No internal connection

6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{CC}	Supply voltage range	−0.5	6.5	V
V _I	Input voltage range ⁽²⁾	−0.5	6.5	V
V _O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	−0.5	6.5	V
V _O	Voltage range applied to any output in the high or low state ⁽²⁾⁽³⁾	−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0	−50	mA
I _{OK}	Output clamp current	V _O < 0	−50	mA
I _O	Continuous output current		±50	mA
	Continuous current through V _{CC} or GND		±100	mA
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level	±2000	V
		Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	Operating	1.65	5.5
		Data retention only	1.5	
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	1.7	
		V _{CC} = 3 V to 3.6 V	2	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	0.7	
		V _{CC} = 3 V to 3.6 V	0.8	
		V _{CC} = 4.5 V to 5.5 V	0.3 × V _{CC}	
V _I	Input voltage	0	5.5	V
V _O	Output voltage	0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65 V	–4	mA
		V _{CC} = 2.3 V	–8	
		V _{CC} = 3 V	–16	
		V _{CC} = 4.5 V	–24	
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4	mA
		V _{CC} = 2.3 V	8	
		V _{CC} = 3 V	16	
		V _{CC} = 4.5 V	24	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V	20	ns/V
		V _{CC} = 3.3 V ± 0.3 V	10	
		V _{CC} = 5 V ± 0.5 V	5	
T _A	Operating free-air temperature	Q-suffix devices	–40	125
		I-suffix devices	–40	85

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC1G08-Q1			UNIT
		DBV	DCK	DRY	
		5 PINS	5 PINS	6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	209.4	244.2	264.4	°C/W
R _{θJCTop}	Junction-to-case (top) thermal resistance	132.5	156.1	166.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	118.1	130.8	142.2	°C/W
ψ _{JT}	Junction-to-top characterization parameter	48.8	47.2	26.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	117.4	130.0	141.6	°C/W
R _{θJCbott}	Junction-to-case (bottom) thermal resistance	–	–	–	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics application report](#).

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{CC}	–40°C to 85°C			–40°C to 125°C RECOMMENDED			UNIT
				MIN	TYP ⁽¹⁾	MAX	MIN	TYP	MAX	
V _{OH}		I _{OH} = –100 μA	1.65 V to 5.5 V	V _{CC} – 0.1			V _{CC} – 0.15			V
		I _{OH} = –4 mA	1.65 V	1.2			1.2			
		I _{OH} = –8 mA	2.3 V	1.9			1.9			
		I _{OH} = –16 mA	3 V	2.4			2.4			
		I _{OH} = –24 mA		2.3			2.3			
		I _{OH} = –32 mA	4.5 V	3.8			3.8			
V _{OL}		I _{OL} = 100 μA	1.65 V to 5.5 V	0.1			0.1			V
		I _{OL} = 4 mA	1.65 V	0.45			0.45			
		I _{OL} = 8 mA	2.3 V	0.3			0.3			
		I _{OL} = 16 mA	3 V	0.4			0.4			
		I _{OL} = 24 mA		0.55			0.55			
		I _{OL} = 32 mA	4.5 V	0.55			0.55			
I _I	A or B inputs	V _I = 5.5 V or GND	0 to 5.5 V	±5			±5			μA
I _{off}		V _I or V _O = 5.5 V	0	±10			±10			μA
I _{CC}		V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V	10			10			μA
ΔI _{CC}		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V	500			500			μA
C _I		V _I = V _{CC} or GND	3.3 V	4			4			pF

 (1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Switching Characteristics, T_A = –40°C to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 125°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	1	10	1	7.5	1	6.5	1	6	ns

6.7 Switching Characteristics, T_A = –40°C to 85°C

over recommended operating free-air temperature range, (unless otherwise noted) (see Figure 4)

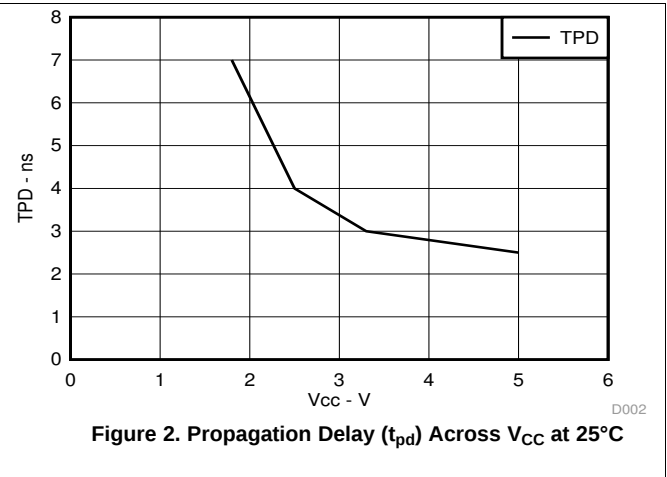
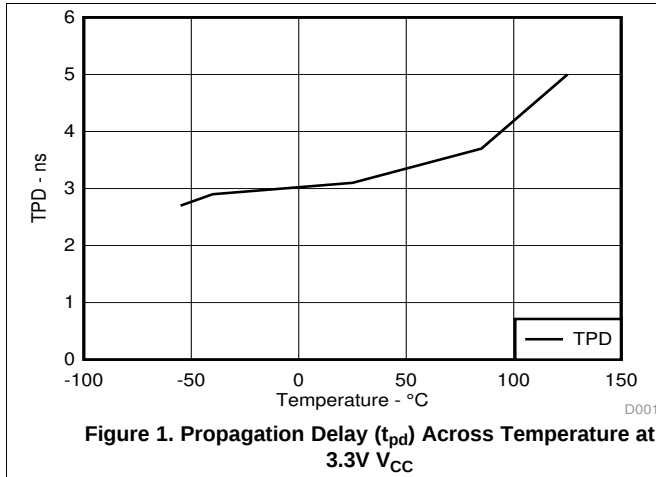
PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 85°C								UNIT
			V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	2.4	8	1.1	5.5	1	4.5	1	4	ns

6.8 Operating Characteristics

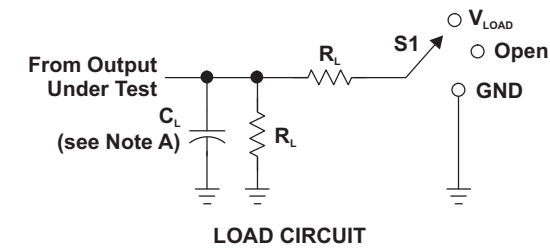
 T_A = 25°C

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C _{pd}	Power dissipation capacitance	f = 10 MHz	21	24	26	31	pF

6.9 Typical Characteristics

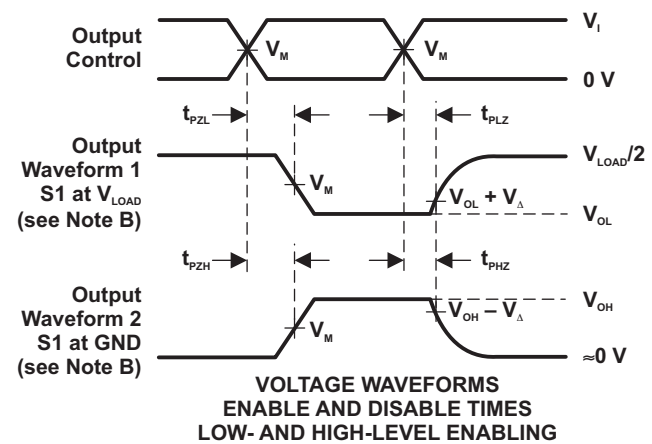
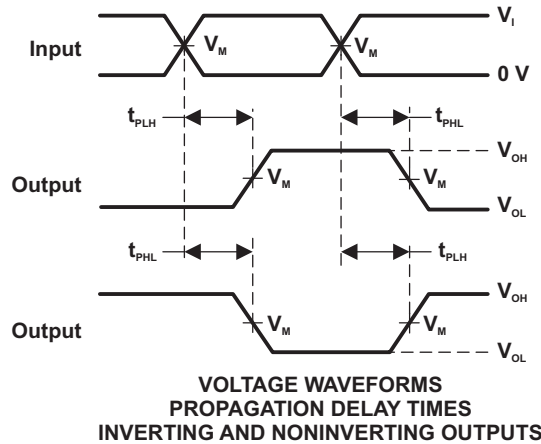
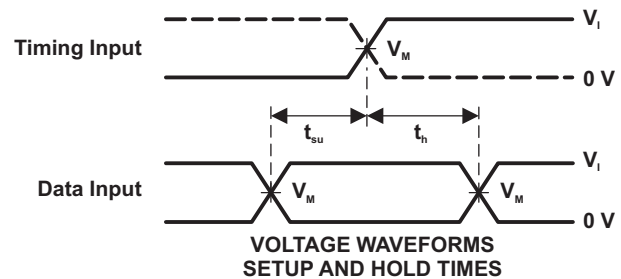
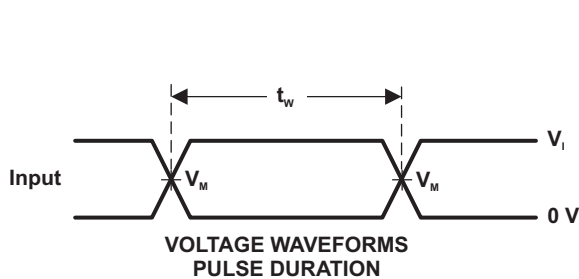


7 Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

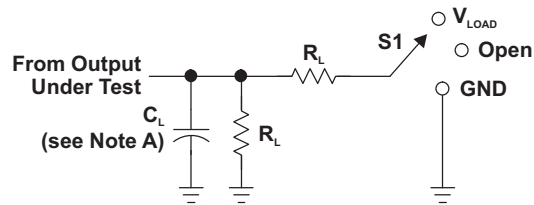
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	15 pF	1 M Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.3 V



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_o = 50\ \Omega$.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

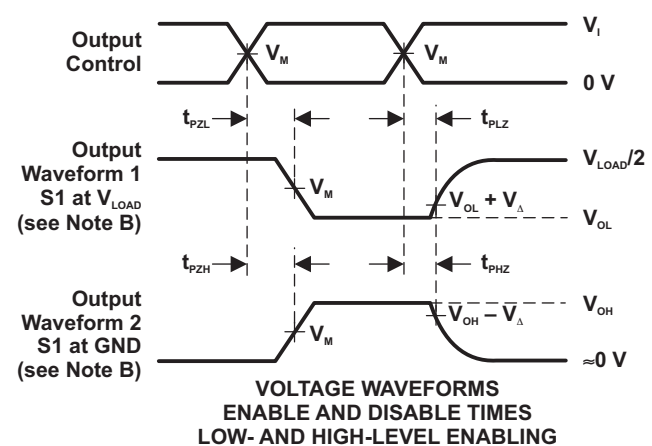
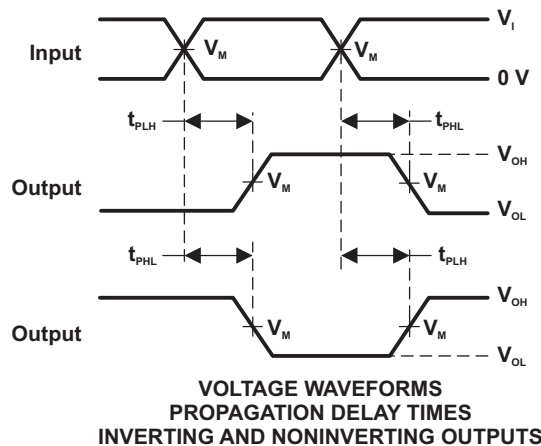
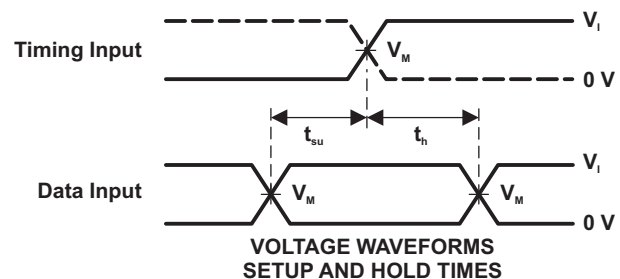
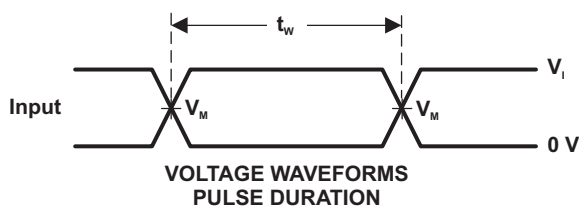
Parameter Measurement Information (continued)



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\text{ }\Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{on} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LVC1G08Q device contains one 2-input positive AND gate device and performs the Boolean function $Y = A \cdot B$ or $Y = \overline{A + B}$. This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram

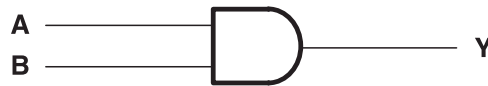


Figure 5. Positive Logic

8.3 Feature Description

- Wide operating voltage range.
 - Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- I_{off} feature allows voltages on the inputs and outputs when V_{CC} is 0 V.

8.4 Device Functional Modes

Table 1. Function Table

INPUTS		OUTPUT Y
A	B	
H	H	H
L	X	L
X	L	L

9 Application and Implementation

9.1 Application Information

The SN74LVC1G08Q is a high-drive CMOS device that can be used for implementing AND logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5 V tolerant allowing it to translate down to V_{CC} .

9.2 Typical Application

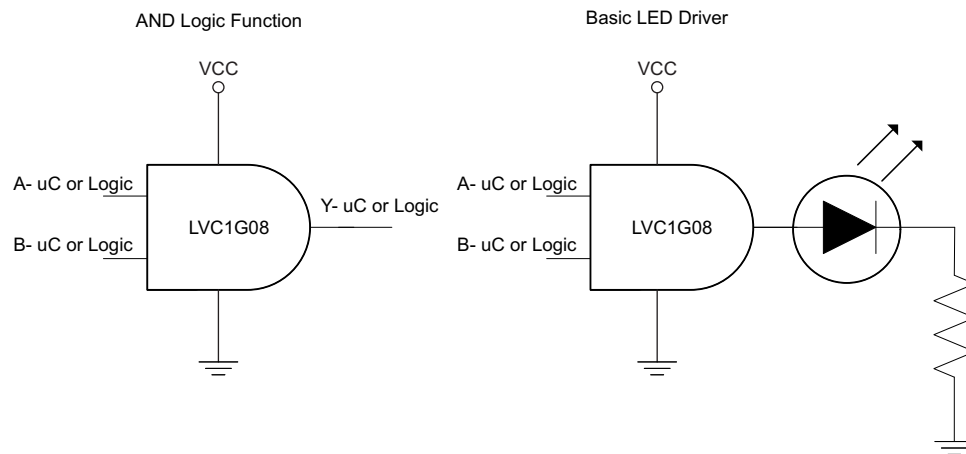


Figure 6. Typical Application Example

9.2.1 Design Requirements

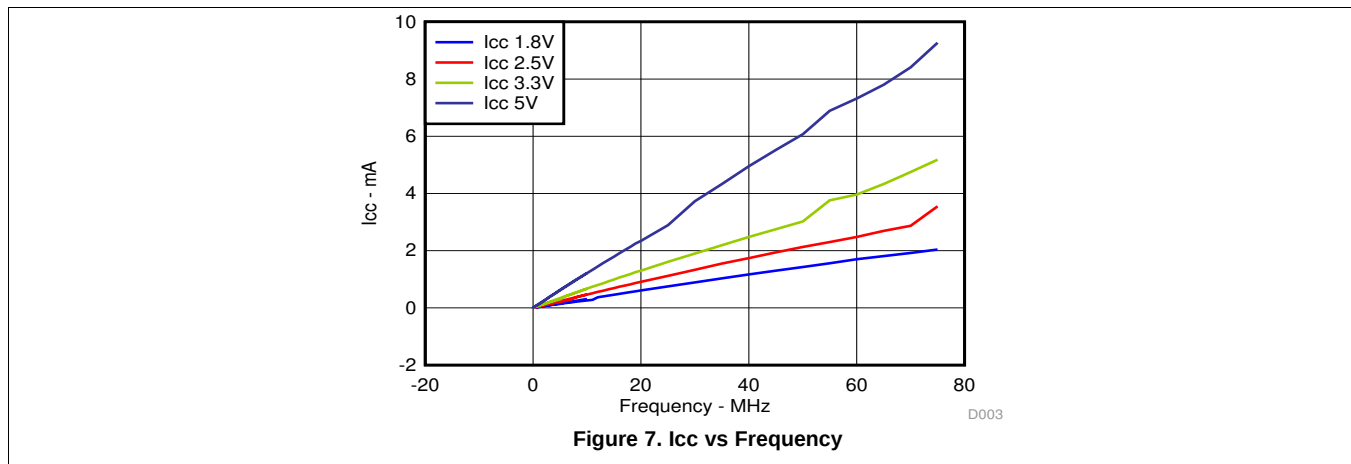
This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions
 - Rise time and fall time specs. See $(\Delta t/\Delta V)$ in the [Recommended Operating Conditions](#) table.
 - Specified high and low levels. See $(V_{IH}$ and $V_{IL})$ in the [Recommended Operating Conditions](#) table.
 - Inputs are overvoltage tolerant allowing them to go as high as $(V_I \text{ max})$ in the [Recommended Operating Conditions](#) table at any valid V_{CC} .
2. Recommend Output Conditions
 - Load currents should not exceed $(I_O \text{ max})$ per output and should not exceed total current (continuous current through V_{CC} or GND) for the part. These limits are located in the [Absolute Maximum Ratings](#) table.
 - Outputs should not be pulled above V_{CC} .

Typical Application (continued)

9.2.3 Application Curves



10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each Vcc pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF capacitor is recommended and if there are multiple Vcc pins then 0.01-μF or 0.022-μF capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to Gnd or Vcc whichever make more sense or is more convenient.

11.2 Layout Example

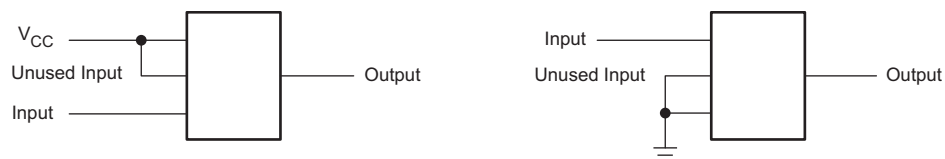


Figure 8. Layout Example

12 器件和文档支持

12.1 商标

All trademarks are the property of their respective owners.

12.2 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.3 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74LVC1G08QDBVRQ1G4	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
74LVC1G08QDBVRQ1G4.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
74LVC1G08QDCKRQ1G4	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CEO
74LVC1G08QDCKRQ1G4.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CEO
SN74LVC1G08IDCKRQ1	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CEO
SN74LVC1G08IDCKRQ1.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CEO
SN74LVC1G08IDCKRQ1.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CEO
SN74LVC1G08QDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
SN74LVC1G08QDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
SN74LVC1G08QDBVRQ1.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)
SN74LVC1G08QDCKRQ1	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CEJ, CEO)
SN74LVC1G08QDCKRQ1.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(CEJ, CEO)
SN74LVC1G08QDCKRQ1.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(CEJ, CEO)
SN74LVC1G08QDRYRQ1	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	EM
SN74LVC1G08QDRYRQ1.B	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	EM

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF SN74LVC1G08-Q1 :

- Catalog : [SN74LVC1G08](#)
- Enhanced Product : [SN74LVC1G08-EP](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G08QDBVRQ1G4	SOT-23	DBV	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
74LVC1G08QDCKRQ1G4	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDRYRQ1	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS

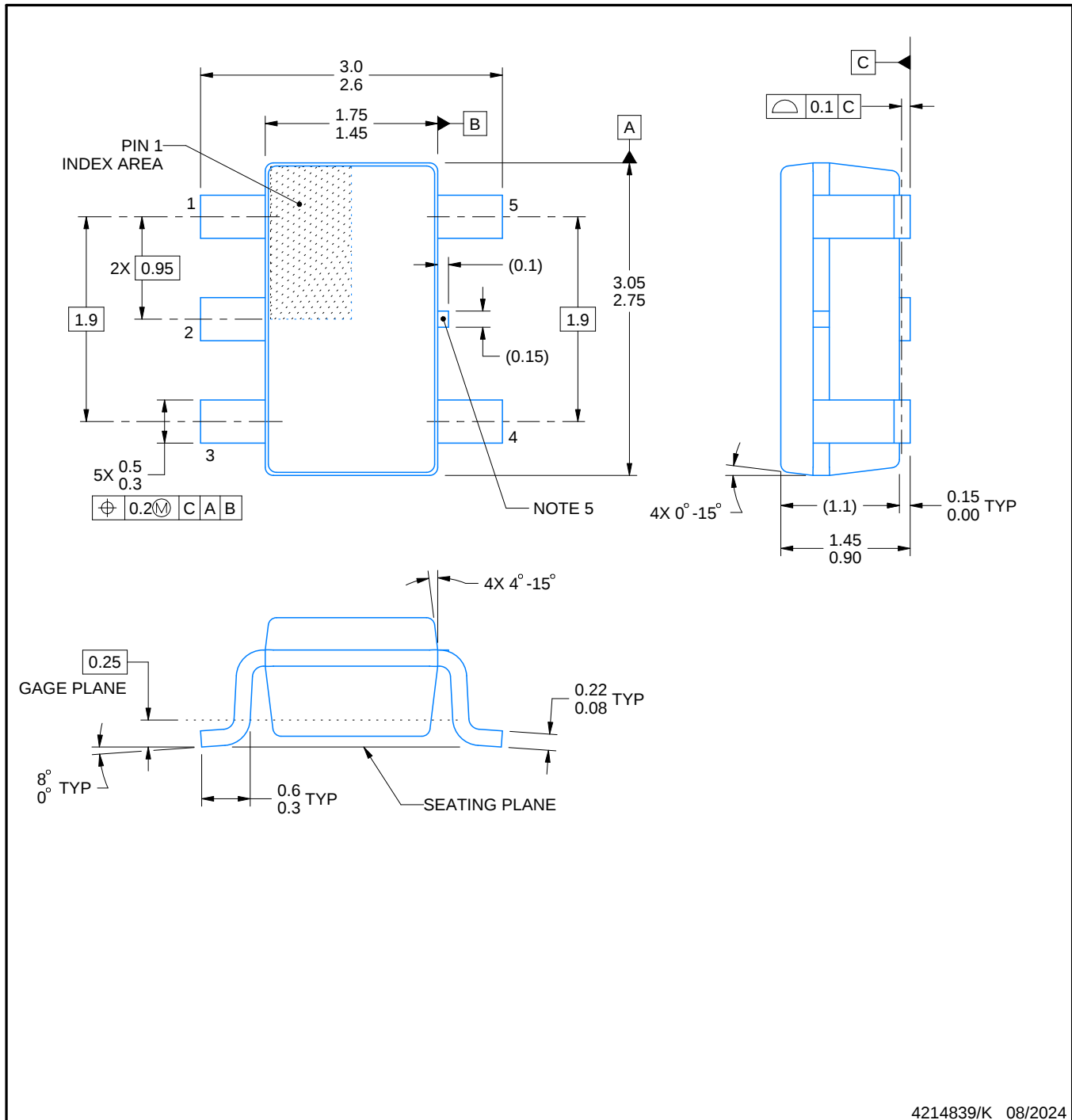


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G08QDBVRQ1G4	SOT-23	DBV	5	3000	180.0	180.0	18.0
74LVC1G08QDCKRQ1G4	SC70	DCK	5	3000	200.0	183.0	25.0
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
SN74LVC1G08QDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
SN74LVC1G08QDRYRQ1	SON	DRY	6	5000	189.0	185.0	36.0

DBV0005A**PACKAGE OUTLINE****SOT-23 - 1.45 mm max height**

SMALL OUTLINE TRANSISTOR



4214839/K 08/2024

NOTES:

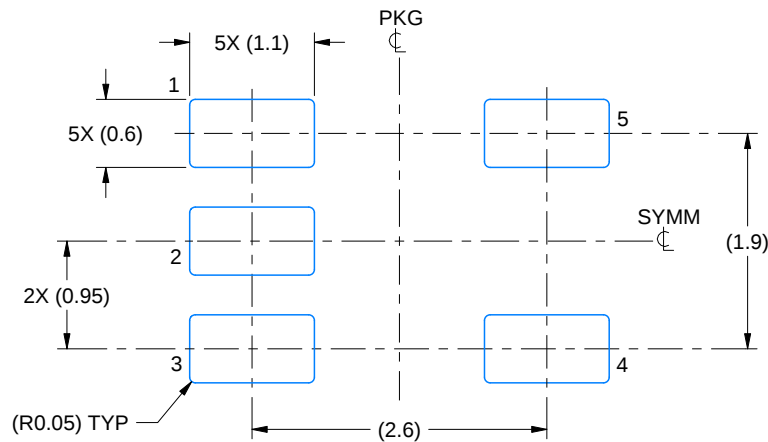
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

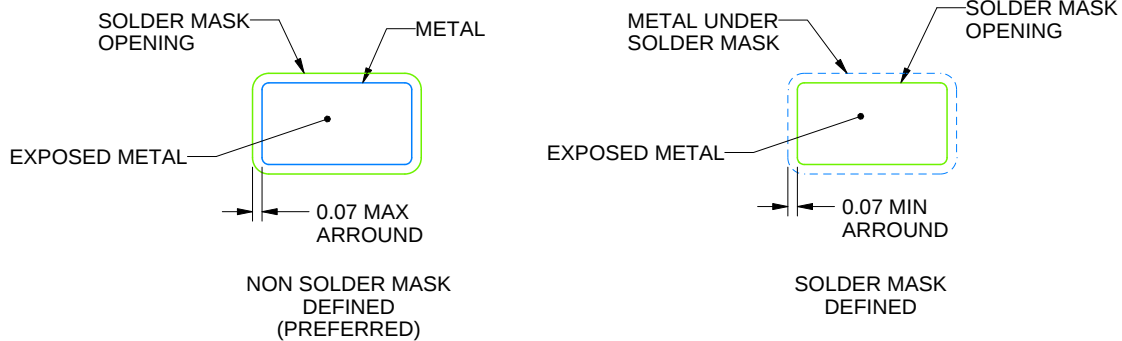
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

DRY 6

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4207181/G



PACKAGE OUTLINE

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

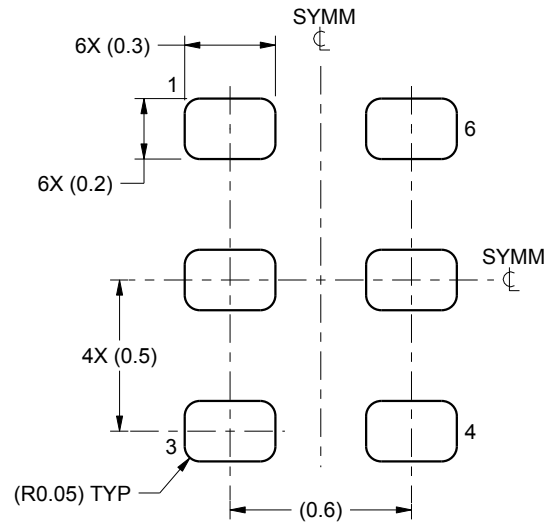
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

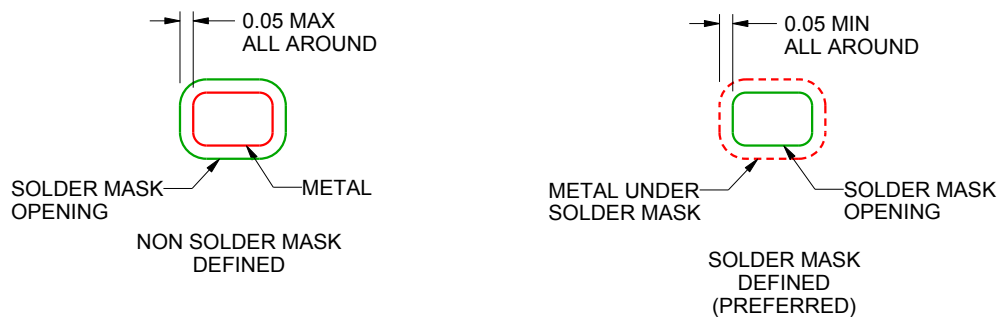
DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
1:1 RATIO WITH PKG SOLDER PADS
SCALE:40X



SOLDER MASK DETAILS

4222207/B 02/2016

NOTES: (continued)

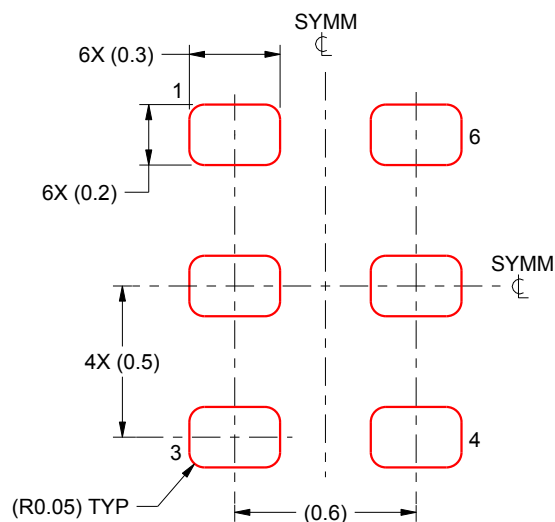
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/sluea271).

EXAMPLE STENCIL DESIGN

DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

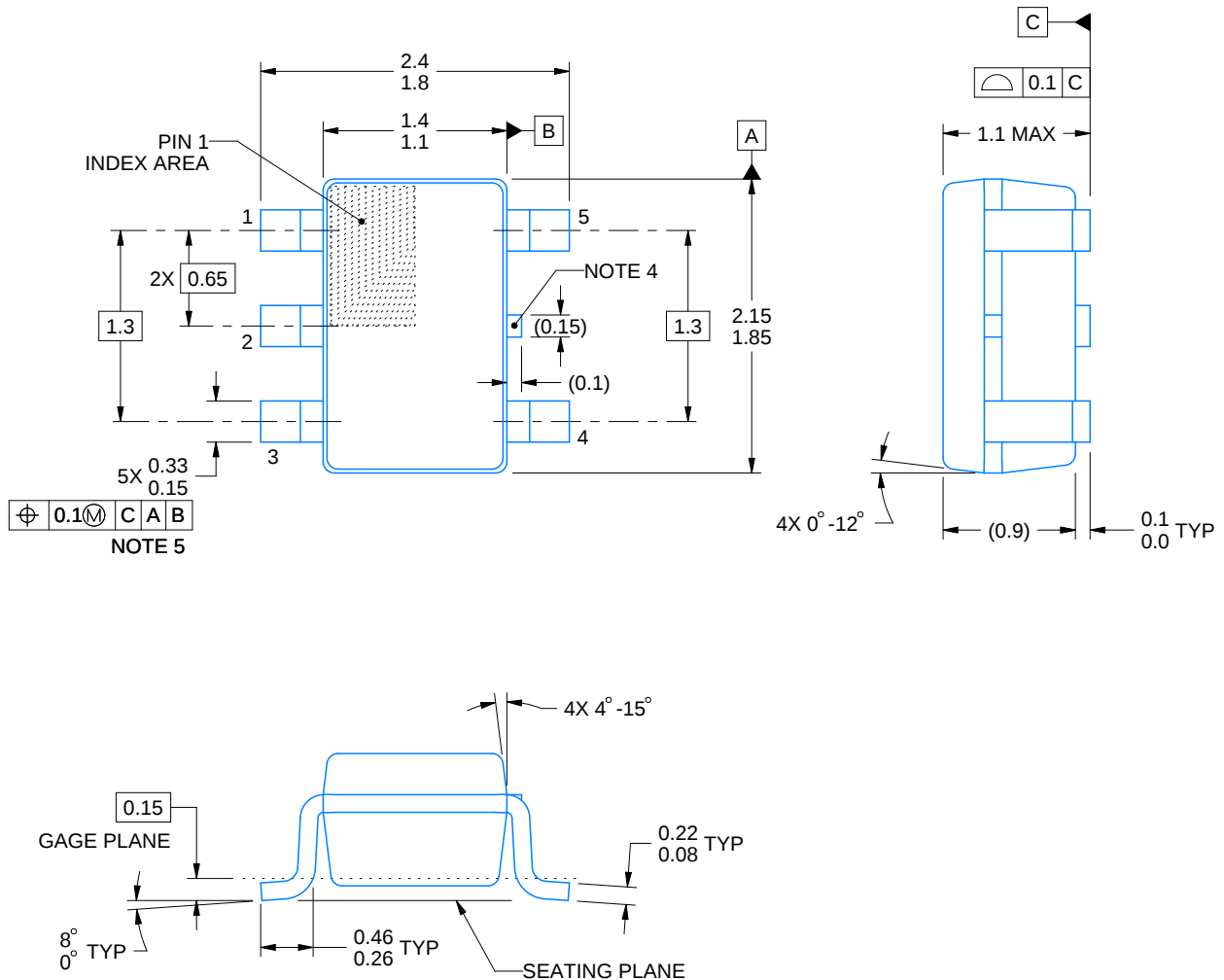


SOLDER PASTE EXAMPLE
BASED ON 0.075 - 0.1 mm THICK STENCIL
SCALE:40X

4222207/B 02/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



4214834/G 11/2024

NOTES:

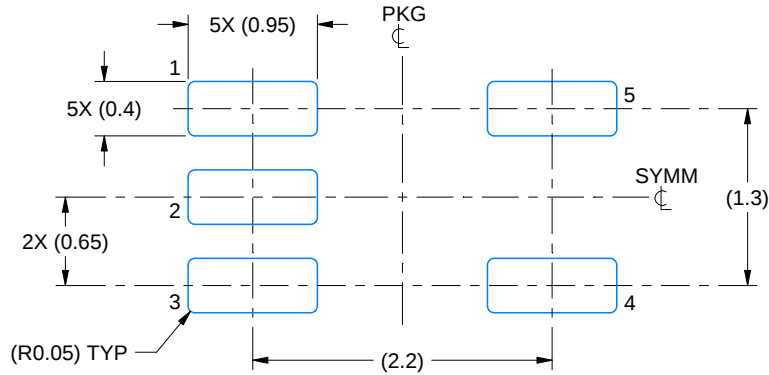
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

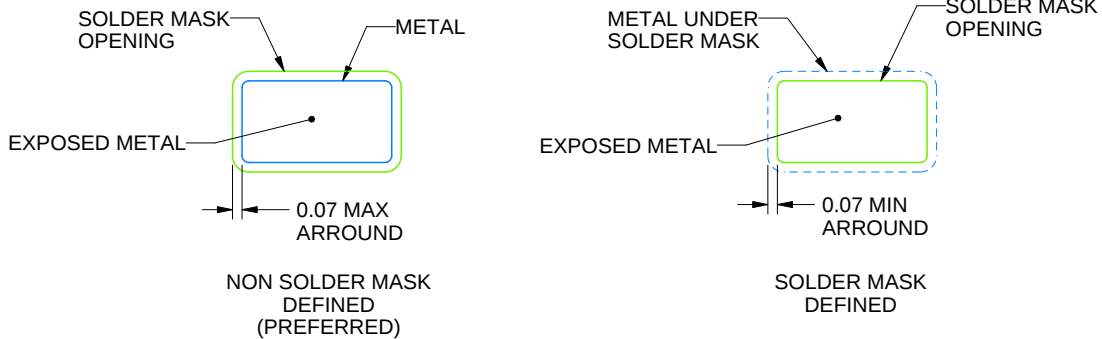
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

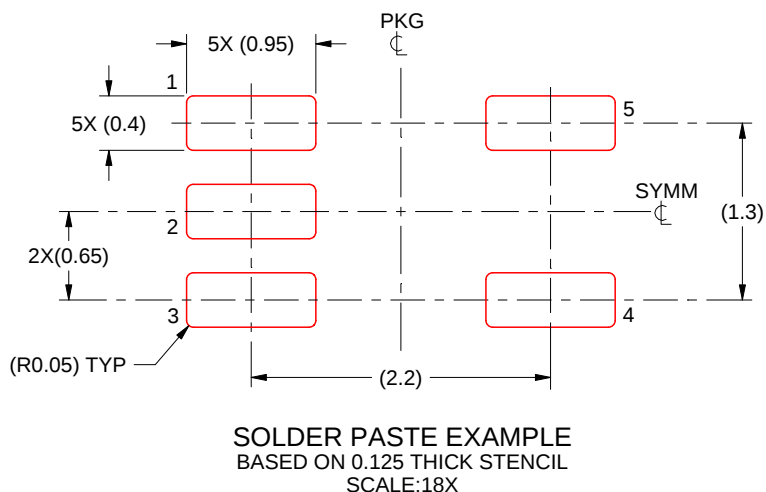


SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

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